

Small signal switching Diodes

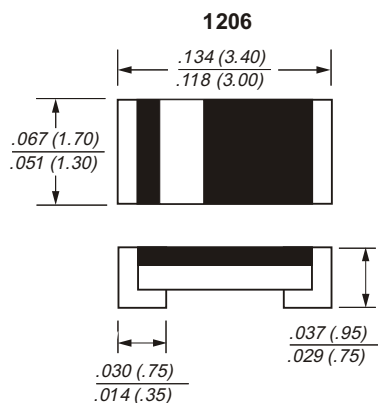
Foward Power Dissipation 400mW

FEATURES

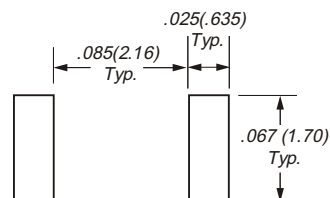
- Silicon epitaxial planar diode
SMD chip pattern, available in various dimension included 0805 & 0603
- Fast switching diode.

MECHANICAL DATA

- Case : 1206
- Polarity : Color band denotes cathode
- Weight : 0.01 grams



Mounting Pad Layout



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase, half wave, 60Hz, resistive or inductive load.

For capacitive load, derate current by 20%

PARAMETER	SYMBOL	Value	UNIT
Reverse voltage	VR	100	V
Peak reverse voltage	VRM	100	V
Forward continuous current	IFM	300	mA
Average rectified current sin half wave rectification with resistive load	IF(av)	150	mA
Surge forward current t<1s and Tj=25	IFSM	500	mA
t<=8.3mS and Tj=25		1000	
Forward voltage If=10mA	VF	1.0	V
If=100mA		1.25	
Leakage current VR=20V	IR	25	nA
VR=75V		5.0	uA
VR=20V, Tj=150		50	uA
Capacitance VF=VR=0V	Ctot	4	pF
Reverse recovery time	trr	4	nS
Power dissipation	Ptot	400	mW
Power derating above 25		3.2	mW/
Typical thermal resistance junction to ambient	R ja	375	K/W
Operating Temperature Range	TJ	-55 to +150	
Storage Temperature Range	Tstg	-55 to +150	

TYPICAL CHARACTERISTICS

Figure 1. Forward Characteristic

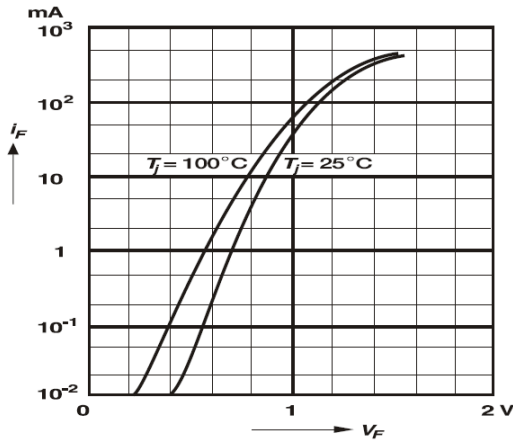


Figure 2. Power De-rating

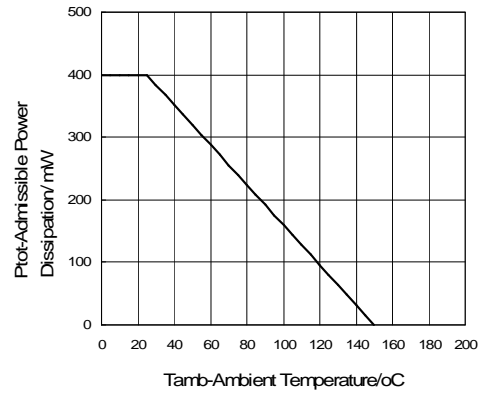


Figure 3. Forward Current De-rating

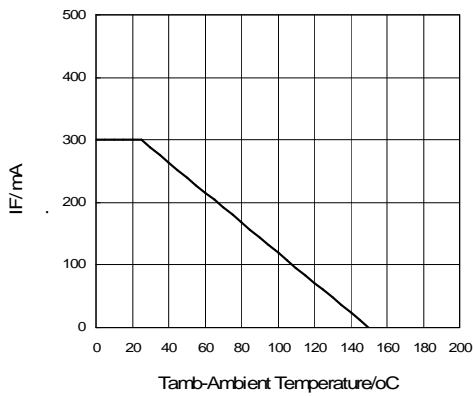


Figure 4. Reverse Voltage De-rating

